

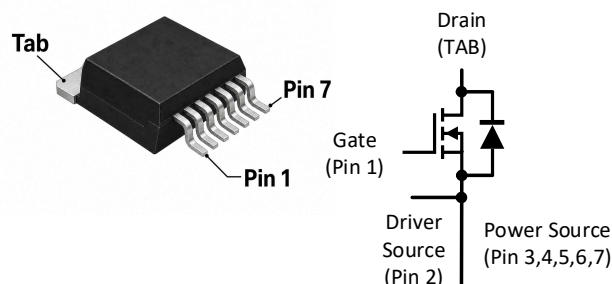
ICE32M120B7 Silicon Carbide Power MOSFET

Features

- 1200V 31.5mohm SiC MOSFET
- Low on-resistance
- Fast switching speed with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Optimized design for High Power SMPS, EV-Charging, Online UPS/HVDC, String Inverters and Solar power optimizer



Product Summary			
I_D	$T_A=25^\circ\text{C}$	62.5A	Max
$V_{(BR)DSS}$	$T_C=25^\circ\text{C}$	1200V	Min
$r_{DS(on)}$	$V_{GS}=18\text{V}$	31.5m Ω	Typ
Q_g	$V_{DS}=800\text{V}$	86nC	Typ



Maximum ratings^a, at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_c=25^\circ\text{C}$	62.5	A
		$T_c=100^\circ\text{C}$	44.1	
Pulsed drain current	$I_{D, \text{pulse}}$		244	A
Maximum gate source voltage	$V_{GS(max)}$		-10/+22	V
Operational gate source voltage	$V_{GS \text{ op}}$		-5/+18	V
Power dissipation	P_{tot}	$T_c=25^\circ\text{C}$	300	W
		$T_c=100^\circ\text{C}$	150	
Storage temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Operating temperature	T_j		-55 to +175	

^a Pulse width limited by T_{jmax}

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Thermal characteristics

Thermal resistance, junction-case	R_{thJC}		-	-	0.5	°C/W
Soldering temperature, wave soldering only allowed at leads	T_{sold}	1.6mm (0.063in.) from case for 10 s	-	-	260	°C

Electrical characteristics^a, at $T_j=25^{\circ}\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	1200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=11mA, T_j=25^{\circ}\text{C}$	2	2.7	4	
		$V_{DS}=V_{GS}, I_D=11mA, T_j=175^{\circ}\text{C}$	-	1.9	-	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V, T_j=25^{\circ}\text{C}$	-	0.1	50	μA
		$V_{DS}=1200V, V_{GS}=0V, T_j=175^{\circ}\text{C}$	-	1	-	
Gate source leakage current	I_{GSS}	$V_{GS}=-10/+22V, V_{DS}=0V$	-	-	± 100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=18V, I_D=40A, T_j=25^{\circ}\text{C}$	-	31.5	41	m Ω
		$V_{GS}=18V, I_D=40A, T_j=175^{\circ}\text{C}$	-	59	-	
Gate resistance	R_G	$f=1\text{ MHz}, V_{AC}=30mV$	-	2.1	-	Ω

Dynamic characteristics

Input capacitance	C_{iss}	$V_{DS}=800V, V_{GS}=0V, f=100\text{ kHz}, V_{AC}=30mV$	-	2247	-	pF
Output capacitance	C_{oss}		-	115	-	
Reverse transfer capacitance	C_{rss}		-	9.3	-	
C_{OSS} stored energy	E_{oss}		-	45	-	μJ
Forward transconductance	g_{FS}	$V_{DS}=20V, I_D=40A$	-	26	-	S
Turn-on delay time	$t_{d(on)}$	$V_{DS}=800V, V_{GS}=-5/+18V, I_D=40A, R_G=4.7\Omega$ (External), $T_j=25^{\circ}\text{C}$	-	10	-	ns
Rise time	t_r		-	16	-	
Turn-off delay time	$t_{d(off)}$		-	23	-	
Fall time	t_f		-	11	-	
Turn-on switching energy	E_{ON}		-	207	-	μJ
Turn-off switching energy	E_{OFF}		-	79	-	

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Dynamic characteristics

Turn-on delay time	$t_{d(on)}$	$V_{DS}=800V, V_{GS}=-5/+18V, I_D=40A, R_G=4.7\Omega$ (External), $T_j=175^\circ C$	-	11	-	ns
Rise time	t_r		-	21	-	
Turn-off delay time	$t_{d(off)}$		-	27	-	
Fall time	t_f		-	12	-	
Turn-on switching energy	E_{ON}		-	362	-	μJ
Turn-off switching energy	E_{OFF}		-	84	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DS}=800V, I_D=40A, V_{GS}=-5 \text{ to } +18V$	-	19	-	nC
Gate to drain charge	Q_{gd}		-	24	-	
Gate charge total	Q_g		-	86	-	

Reverse Diode

Continuous forward current	I_S	$V_{GS}=-5V$	-	-	62.5	A
Diode forward voltage	V_{SD}	$V_{GS}=-5V, I_{SD}=20A, T_j=25^\circ C$	-	3.9	-	V
		$V_{GS}=-5V, I_{SD}=20A, T_j=175^\circ C$	-	3.4	-	
Reverse recovery time	t_{rr}	$V_{GS}=-5V, V_{RR}=800V, I_{SD}=40A, d_iF/d_t=5010 \text{ A}/\mu s, T_j=25^\circ C$	-	13	-	ns
Reverse recovery charge	Q_{rr}		-	152	-	nC
Peak reverse recovery current	I_{rm}		-	20	-	A
Reverse recovery time	t_{rr}	$V_{GS}=-5V, V_{RR}=800V, I_{SD}=40A, d_iF/d_t=8330 \text{ A}/\mu s, T_j=175^\circ C$	-	20	-	ns
Reverse recovery charge	Q_{rr}		-	753	-	nC
Peak reverse recovery current	I_{rm}		-	69	-	A

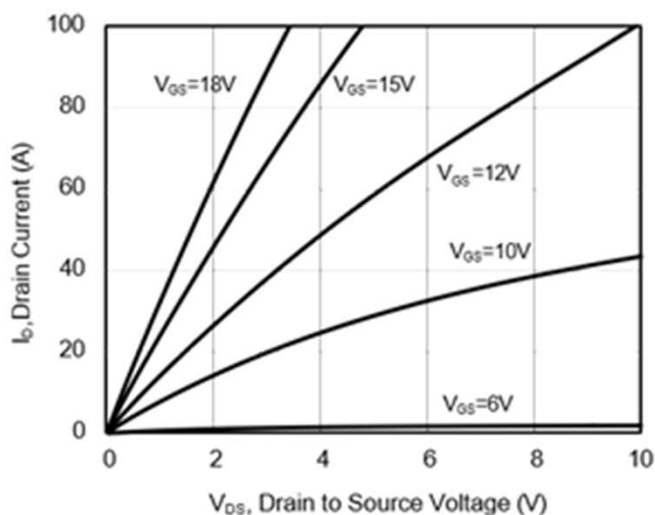


Fig 1. Output Characteristics, $T_j = -55^\circ\text{C}$

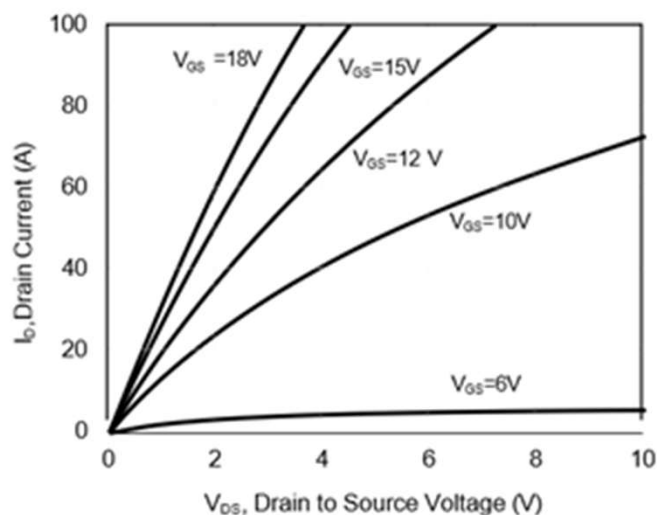


Fig 2. Output Characteristics, $T_j = 25^\circ\text{C}$

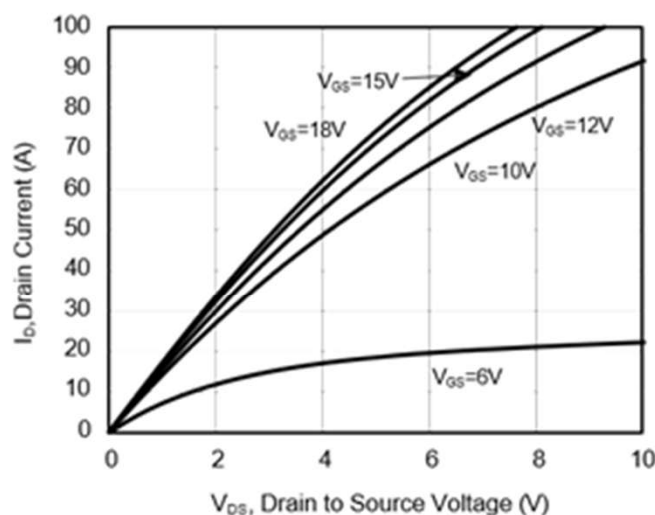


Fig 3. Output Characteristics, $T_j = 175^\circ\text{C}$

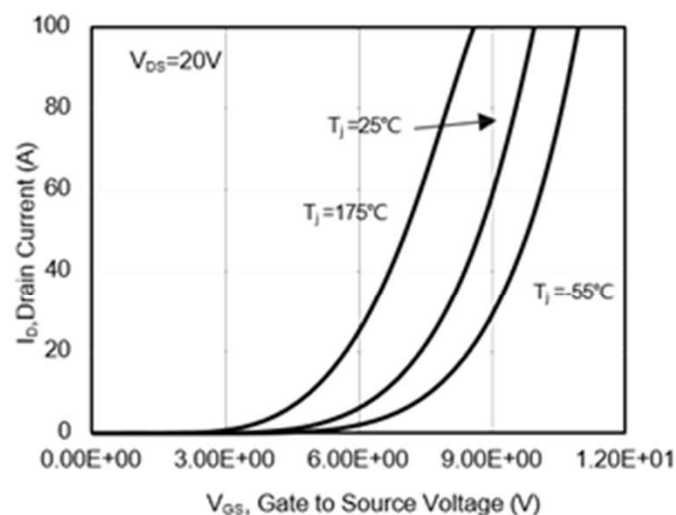


Fig 4. Transfer Characteristics

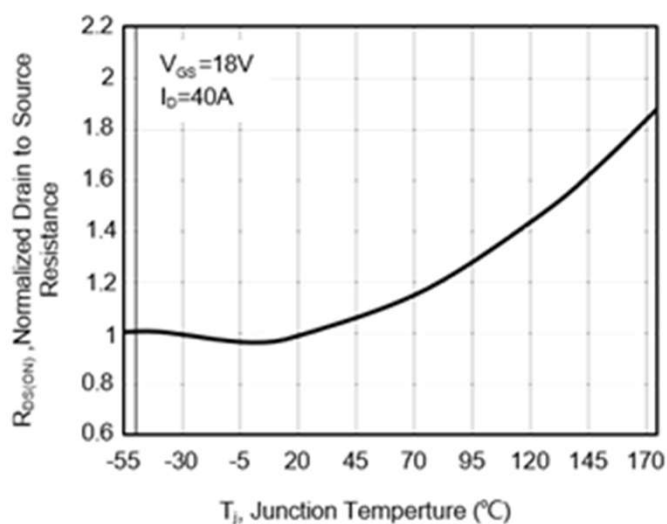


Fig 5. On-Resistance Variation with Temperature

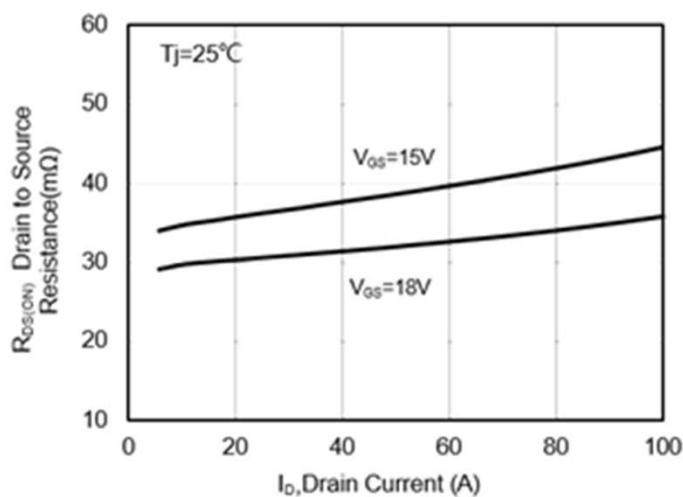


Fig 6. On-Resistance vs Drain Current

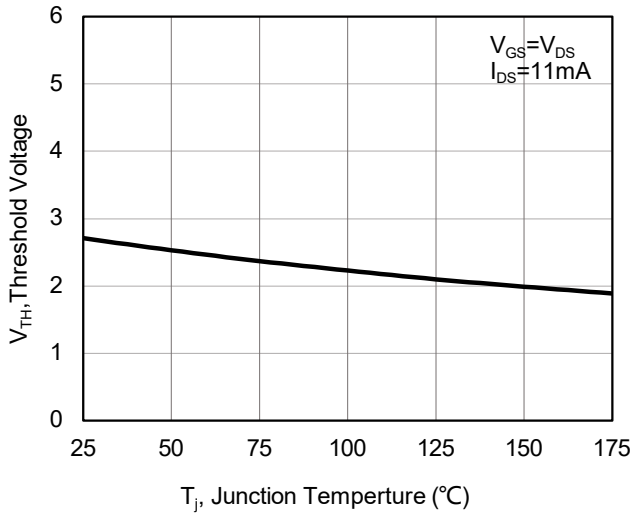


Fig 7. Gate Threshold vs Temperature

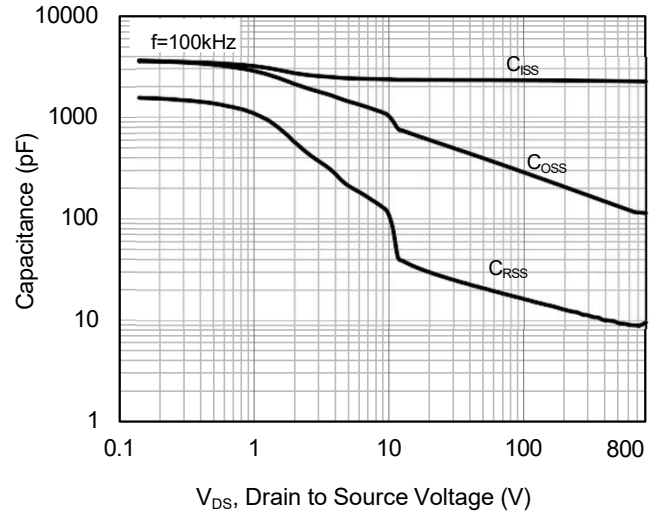


Fig 8. Capacitance Characteristics

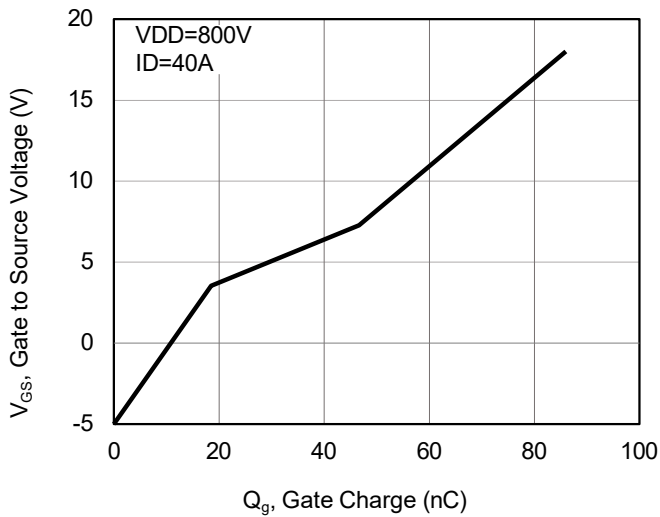


Fig 9. Gate Charge Characteristics

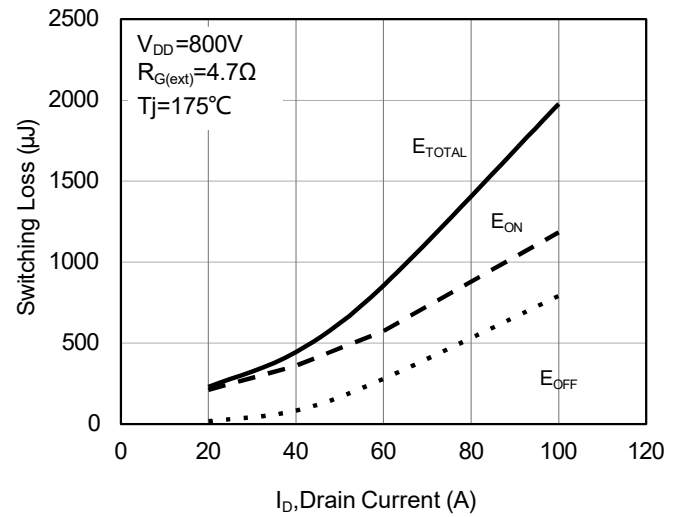


Fig 10. Switching Energy vs. Drain Current

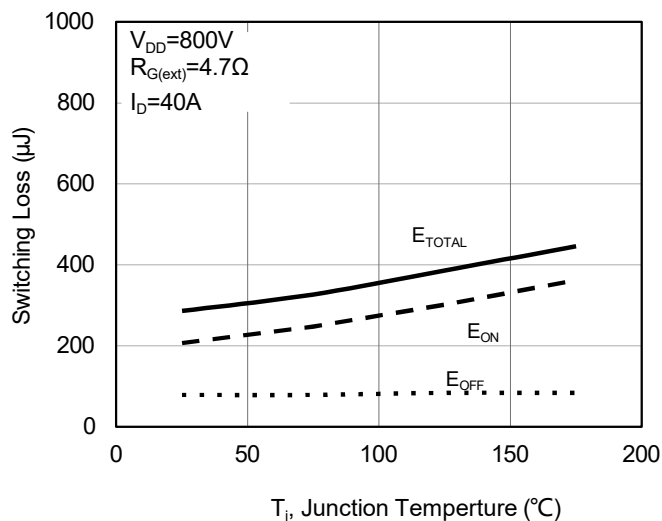


Fig 11. Switching Energy vs. Temperature

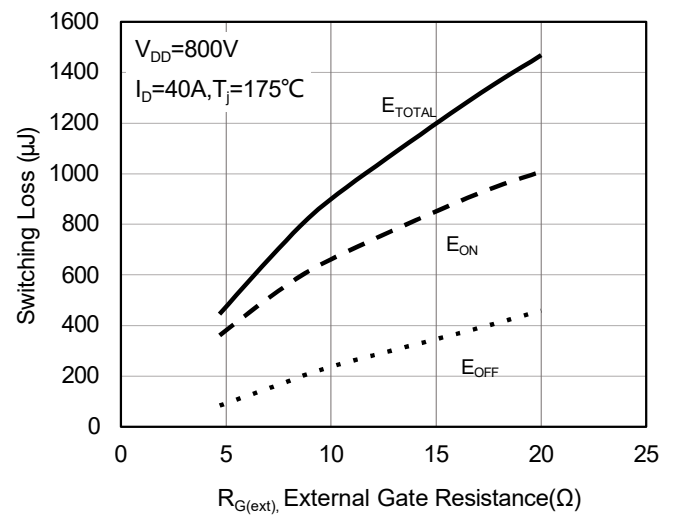


Fig 12. Switching Energy vs. Gate Resistance

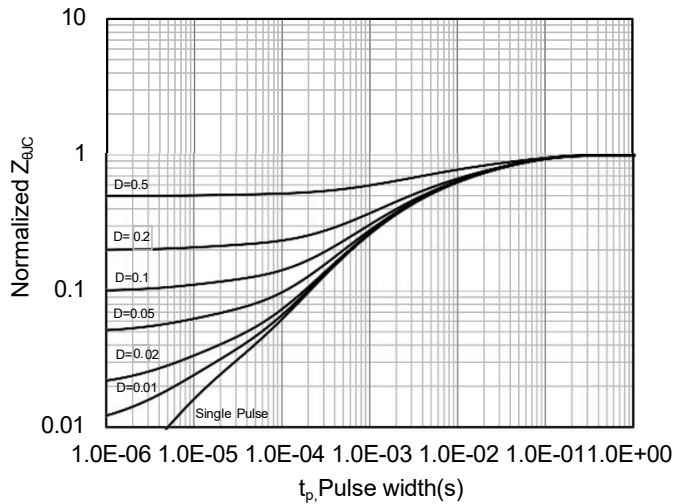


Fig 13. Transient Thermal

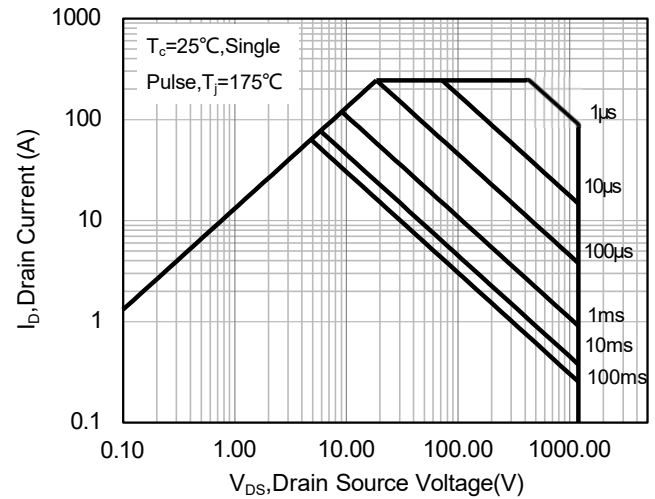


Fig 14. Safe Operating Area

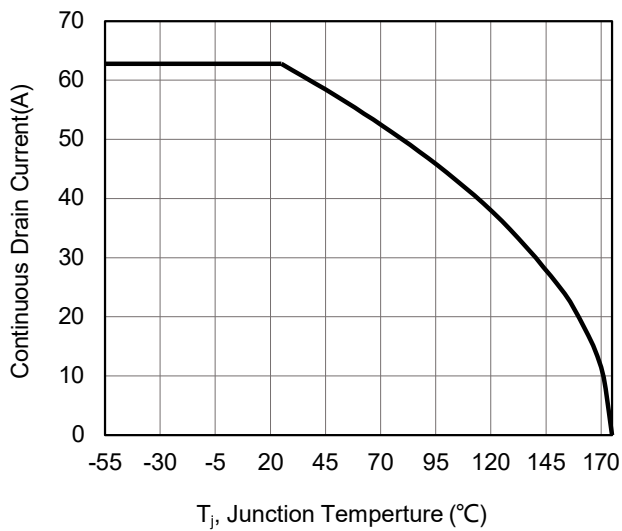


Fig 15. Continuous Drain Current Derating Vs. Case Temperature

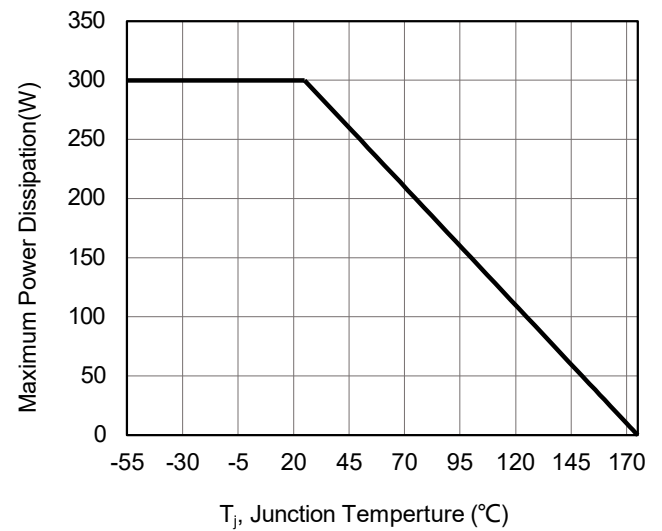


Fig 16. Maximum Power Dissipation Derating vs. Case Temperature

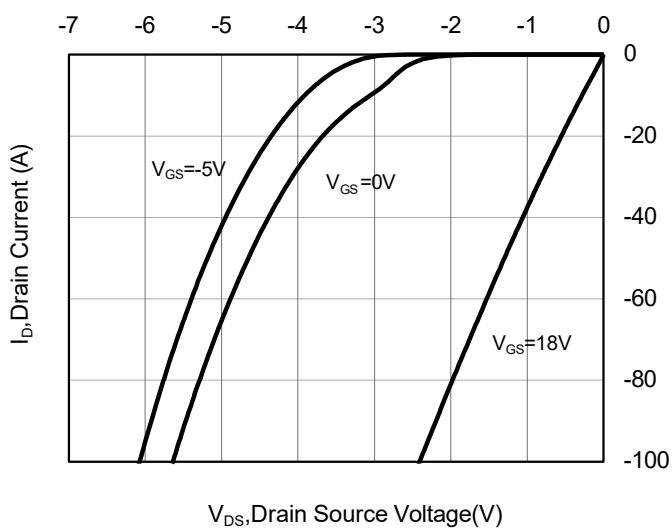


Fig 17. 3rd Quadrant Characteristic at -55 °C

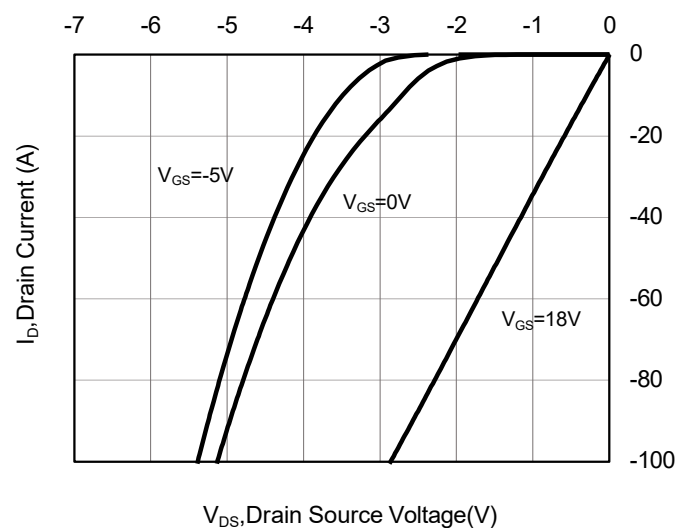


Fig 18. 3rd Quadrant Characteristic at 25 °C

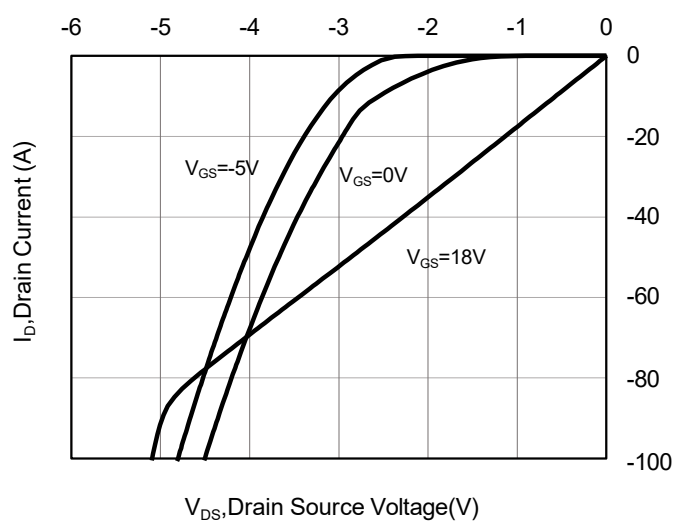
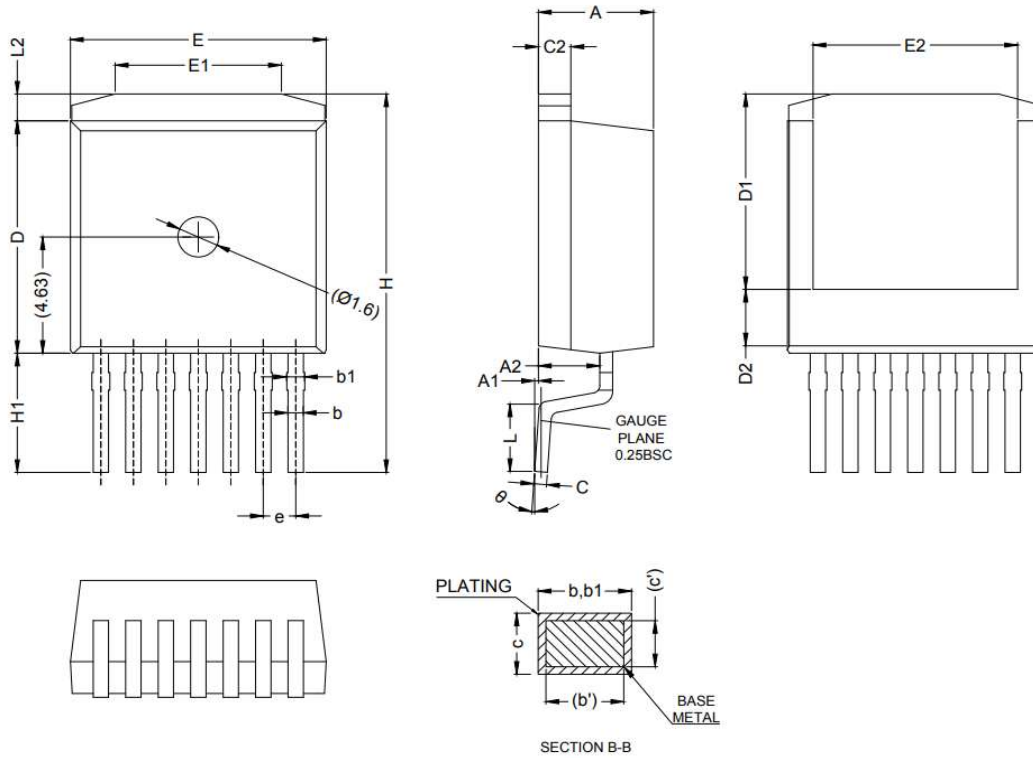


Fig 19. 3rd Quadrant Characteristic at 175 °C

Package Dimension



Items	Min	Max
A	4.30	4.70
A1	-	0.25
A2	2.20	2.60
b	0.52	0.72
b'	0.50	0.70
b1	0.60	0.80
c	0.42	0.62
c'	0.40	0.60
c2	1.07	1.47
D	9.05	9.45
D1	7.58	7.98
D2	2.05	2.45
e	1.27 BSC	
E	9.80	10.20
E1	6.30	6.70
E2	7.80	8.20
L	2.48	2.88
L2	0.87	1.27
H	14.87	15.27
H1	4.55	4.95
θ	0°	8°

Notes:

1. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
2. DIMENSION DO NOT INCLUDE BURR OR MOLD FLASH

Marking Information

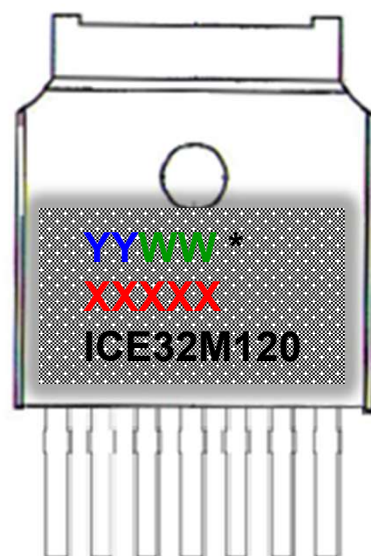
YY = Last two digits of the year

WW = Work week

***** = Site ID

XXXXXX = Lot ID

ICE32M120 = ICE is IceMOS logo and
32M120 is a designated device part
number



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